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TR BDY25B;CEMI;TO3;tranzystor; NPN;6A;200V;87.5W



Dane techniczne:

Nazwa: BDY25B

Typ tranzystora: bipolarny

Kierunek przewodnictwa: NPN

Prąd kolektora: 6A

Napięcie kolektor-emiter: 200V

Moc: 87.5W

Montaż: przewlekany(THT)

Obudowa: TO3

Producent: CEMI

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isc Silicon NPN Power Transistor

BDY25B

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 140V(\text{Min.})$
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = 0.6V(\text{Max}) @ I_C = 2A$
- High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

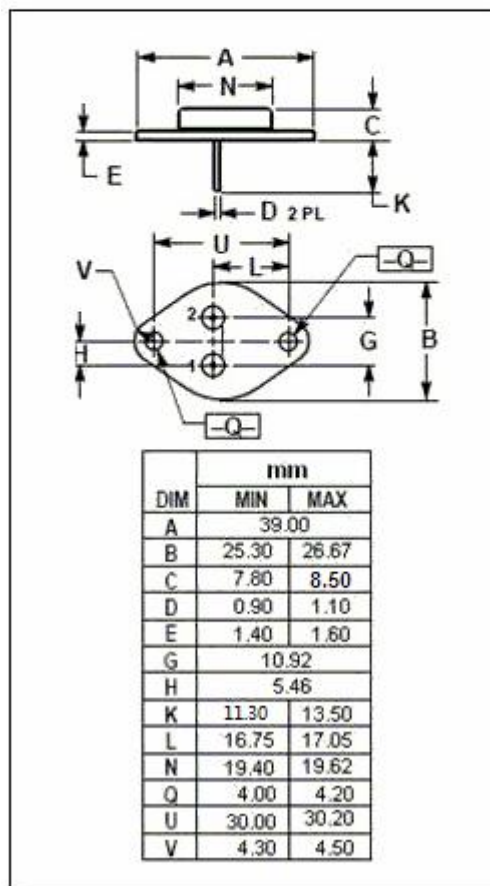
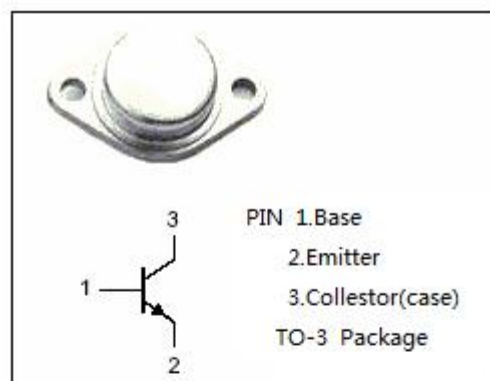
- Designed for LF signal powe amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	200	V
V_{CEO}	Collector-Emitter Voltage	140	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current-Continuous	6	A
I_B	Base Current	3	A
P_C	Collector Power Dissipation@ $T_C = 25^\circ\text{C}$	87.5	W
T_J	Junction Temperature	200	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	2.0	$^\circ\text{C/W}$



isc Silicon NPN Power Transistors**BDY25B****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=50\text{mA}; I_B=0$	140			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}; I_E=0$	200			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2\text{A}; I_B=0.25\text{A}$			0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=2\text{A}; I_B=0.25\text{A}$			1.2	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=180\text{V}; I_E=0$			1.0	mA
I_{CEO}	Collector Cutoff Current	$V_{CE}=140\text{V}; I_B=0$			1.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=10\text{V}; I_C=0$			1.0	mA
h_{FE}	DC Current Gain	$I_C=2\text{A}; V_{CE}=4\text{V}$	30		90	

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